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(54) **TFT-PIN ARRAY SUBSTRATE AND ASSEMBLY STRUCTURE FOR FLAT-PANEL X-RAY DETECTOR**

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(57) **ABSTRACT**

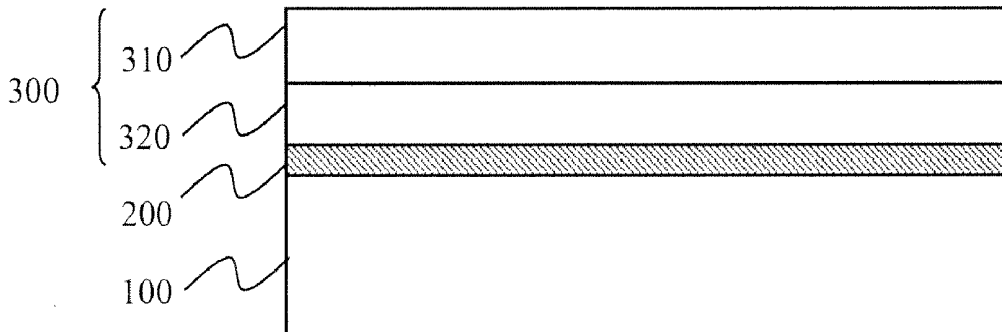
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A TFT-PIN array substrate and an assembly structure for a flat-panel x-ray detector are provided to overcome the problem that the conventional scintillator substrate and TFT-PIN array substrate are neither penetrated by UV-light nor assembled by UV curable LOCA. The metal layer of the PIN photodiode of the TFT-PIN array substrate is perforated to have at least one hole, whereby UV-light can pass through the TFT-PIN array substrate to cure UV curable LOCA. Therefore, UV curable LOCA can be used as an adhesive layer in the assembly structure of a scintillator substrate and a TFT-PIN array substrate to promote the detective quantum efficiency and image quality of a flat-panel X-Ray detector.

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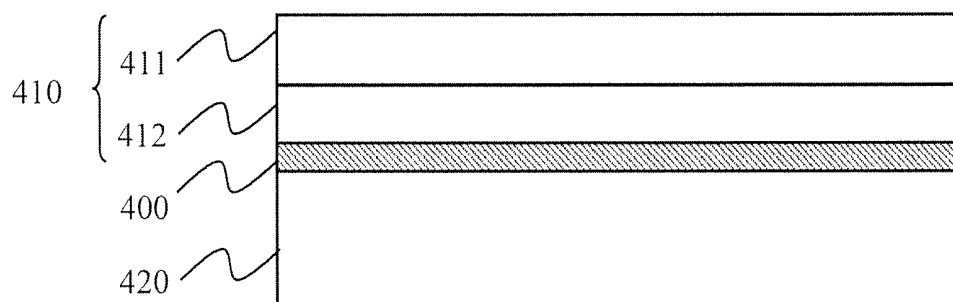


Fig.1(PRIOR ART)

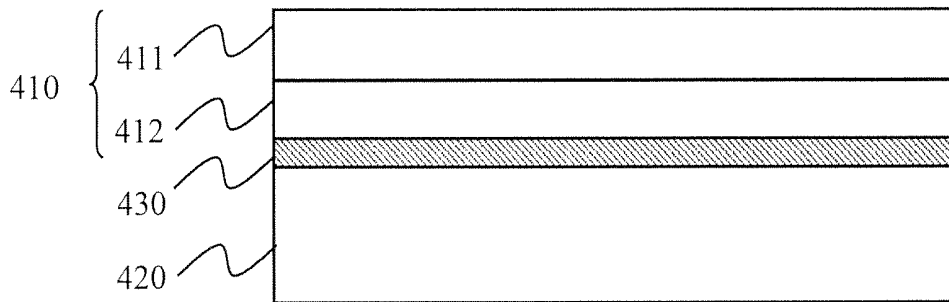


Fig.2(PRIOR ART)

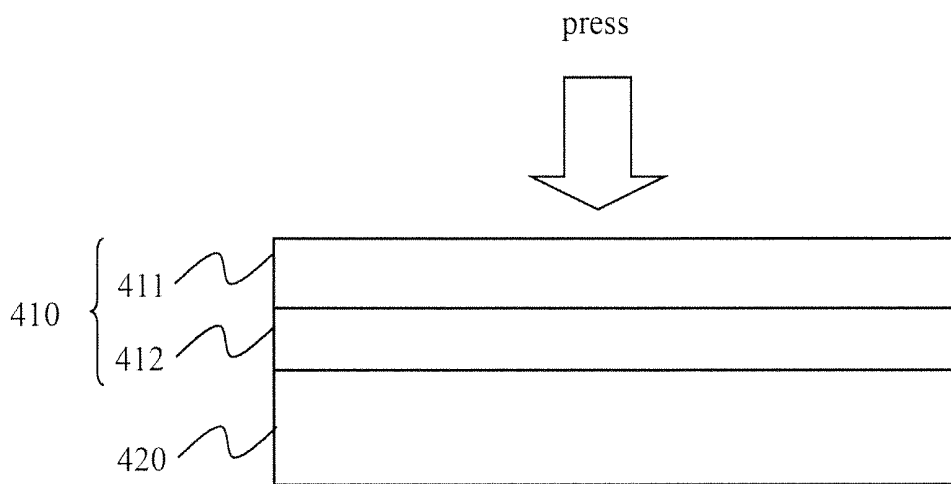


Fig.3(PRIOR ART)

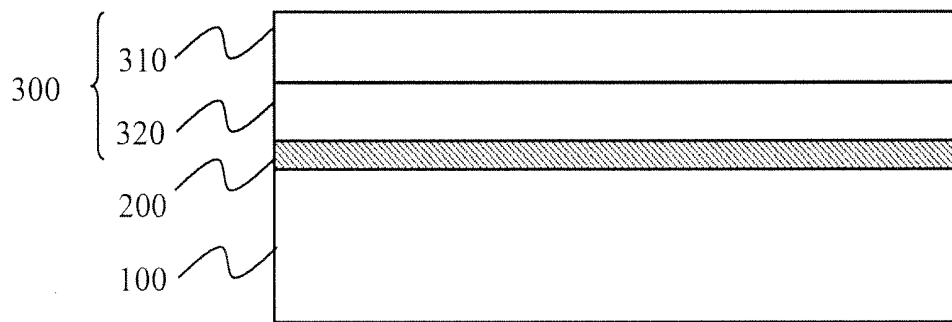


Fig.4

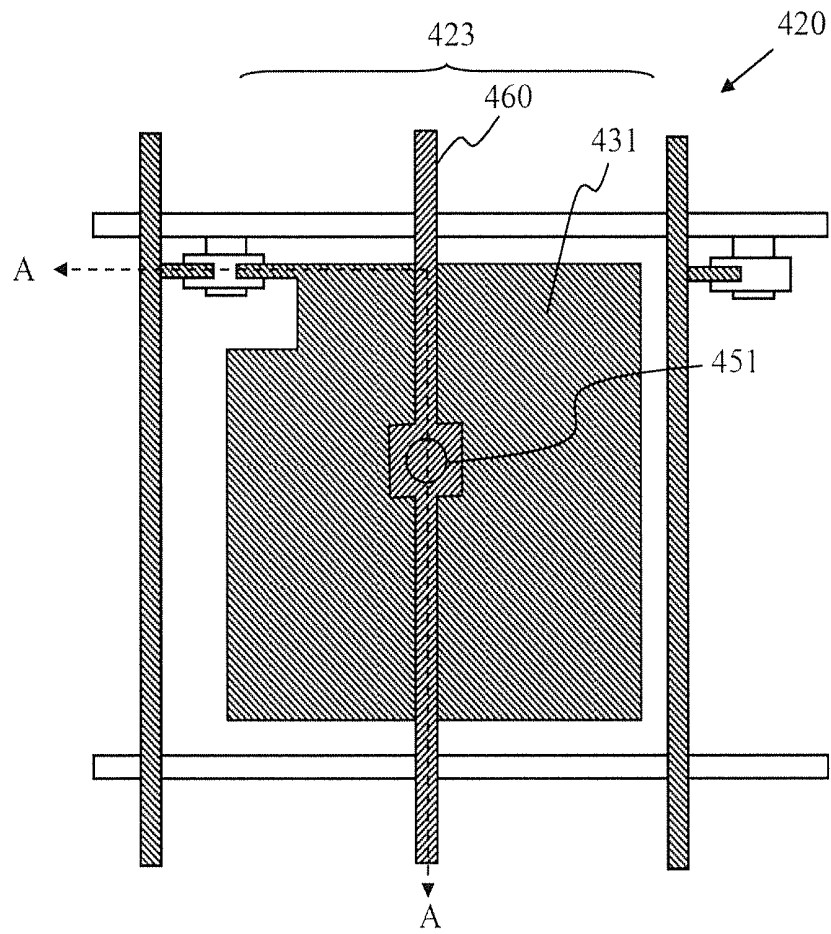


Fig.5A

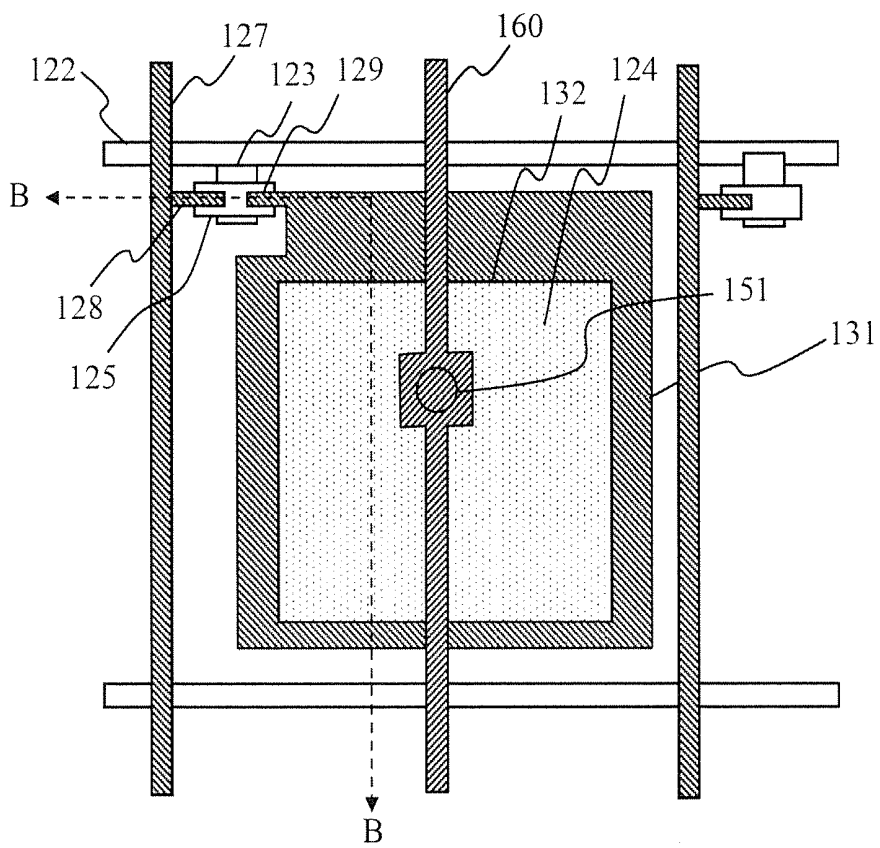


Fig.5B

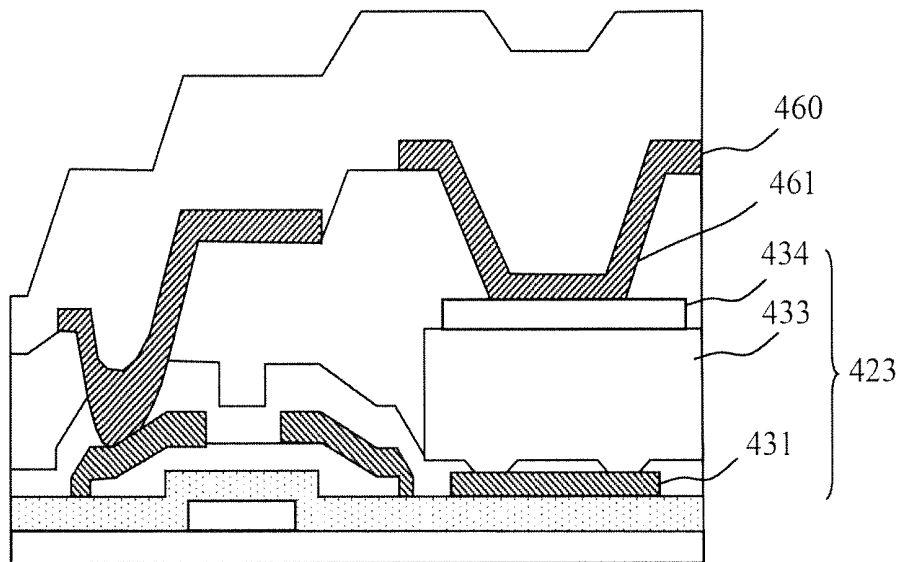


Fig. 6

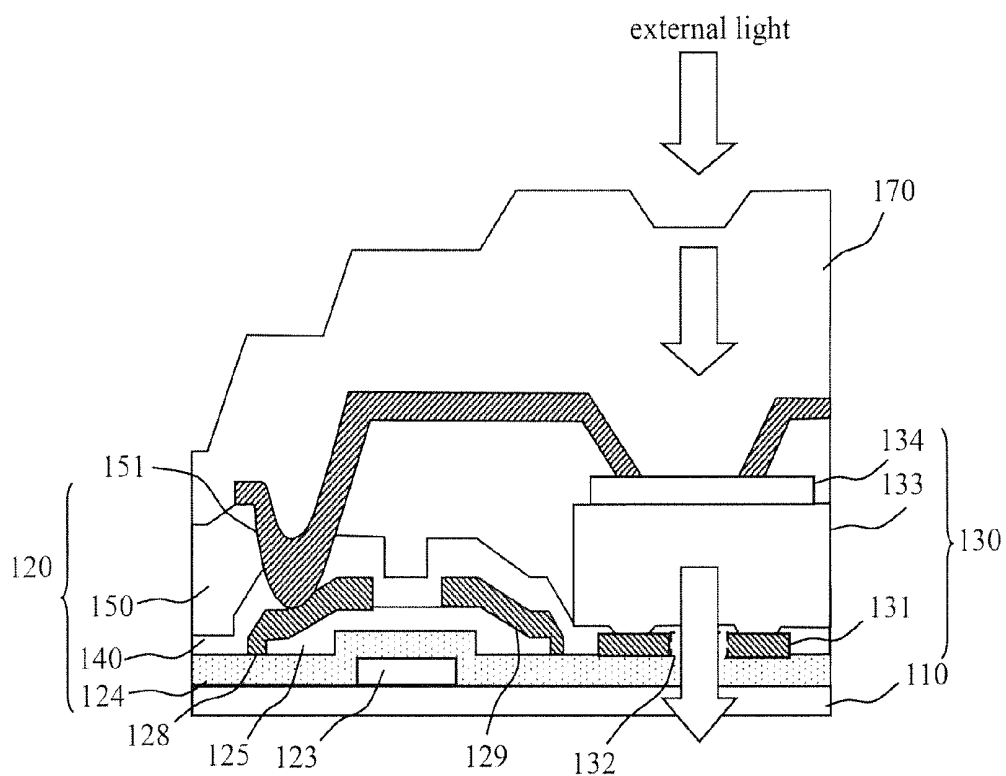


Fig. 7

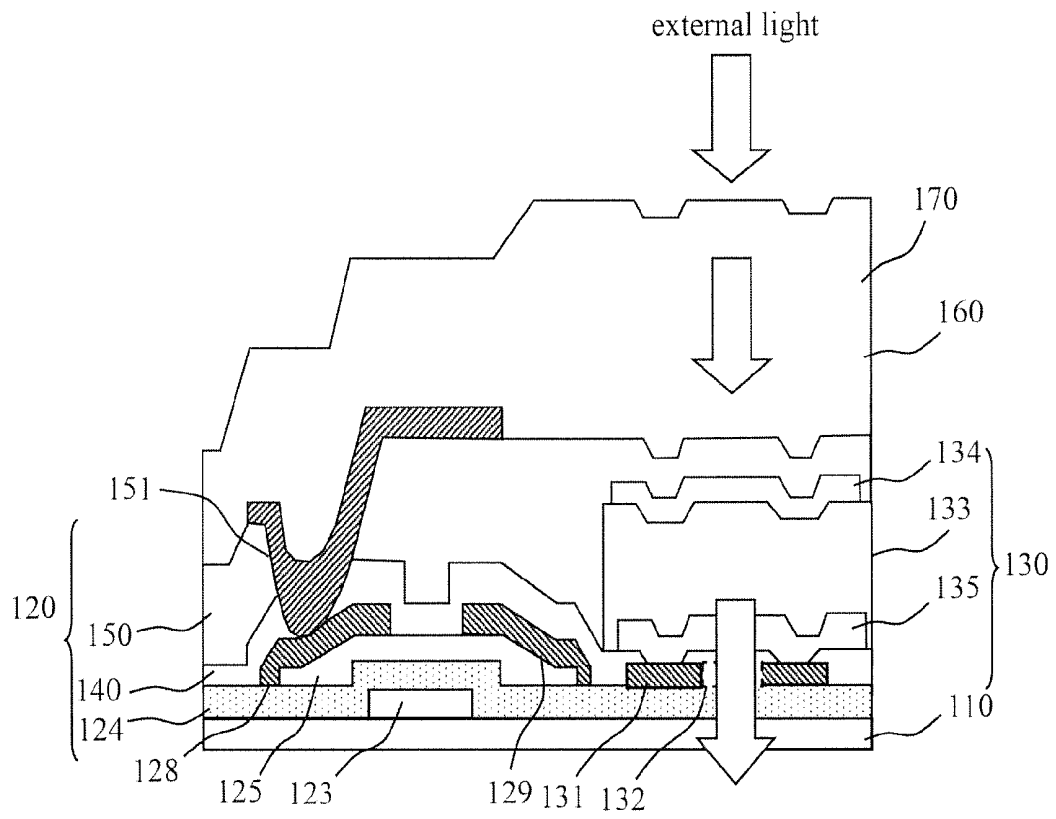


Fig. 8

TFT-PIN ARRAY SUBSTRATE AND ASSEMBLY STRUCTURE FOR FLAT-PANEL X-RAY DETECTOR

BACKGROUND OF THE INVENTION

[0001] 1. Field of the Invention

[0002] The present invention relates to a flat-panel X-ray detector, particularly to a TFT-PIN array substrate and an assembly structure for a flat-panel X-ray detector, which are suitable to a UV curable liquid optically clear adhesive (LOCA) process.

[0003] 2. Description of the Related Art

[0004] FPXD (Flat-Panel X-ray Detector) is an important element in the digital medical image technology. FPXD, with a larger field of detection area and higher detective quantum efficiency (DQE), provides excellent image quality of radiography and simplifies the work flow of diagnostic. TFT-FPX D comprises a scintillator substrate and a TFT-PIN array substrate. The TFT-PIN substrate further comprises a TFT (Thin Film Transistor) and a PIN (Positive-Intrinsic-Negative) photodiode. There are various types of scintillators, but the CsI:TI (TI-doped CsI) scintillator is a frequently-used one. CsI:TI is deposited on an aluminum substrate or a graphite-fiber substrate by a thermal evaporator. The crystal of CsI:TI has a polycrystalline structure or a column structure. The polycrystalline structure has an advantage of simple fabrication parameters and a disadvantage of severe image blur caused by a larger scatter angle. An X-ray beam excites a scintillator to emit visible light. A larger scatter angle of the visible light emitted by the scintillator may cause the neighboring pixels to operate falsely, decrease the spatial resolution, and lower the detective quantum efficiency. The column structure has disadvantages of complicated fabrication parameters of single crystal and low stability of the yield, especially in a large-area FPXD. However, the column structure has an advantage of a smaller scatter angle, which can decrease noise and increase image resolution.

[0005] Below are introduced the conventional assembly structures of a scintillator substrate and a TFT-PIN array substrate. Refer to FIG. 1. PSA (Pressure Sensitive Adhesive) **400** is arranged between a scintillator substrate **410** and a TFT-PIN array substrate **420**, and they are assembled together via pressing them. The PSA-based assembly method is more suitable to assemble a scintillator **412** having a flexible substrate **411** to the TFT-PIN array substrate **420**. Refer to FIG. 2. Ambient temperature-humidity cured or thermoset LOCA (Liquid Optically Clear Adhesive) **430** is arranged between a scintillator substrate **410** and a TFT-PIN array substrate **420**, and they are assembled together via pressing them. The LOCA-based assembly method is more suitable to assemble a scintillator **412** having a rigid substrate **411**, which is made of a hard material (such as aluminum or graphite fiber), to the TFT-PIN array substrate **420**. The LOCA-based assembly method has a disadvantage of long curing time, which is likely to affect yield and alignment precision. Refer to FIG. 3. There is also an assembly method, wherein external pressure is applied to fix a scintillator substrate **410** and a TFT-PIN array substrate **420**. However, the method is likely to generate gaps between the scintillator substrate **410** and the TFT-PIN array substrate **420**. The difference between the refractivities of the air in the gaps and the scintillator **412** would decrease light transmittance and thus causes variation of light transmittance and unevenness of brightness.

[0006] Refer to FIG. 5A and FIG. 6 respectively a diagram showing a conventional TFT-PIN array substrate and a sectional view taken along Section Line A-A in FIG. 5A. The PIN photodiode **423** of the TFT-PIN array substrate **420** includes a metal layer **431**, a photoelectric conduction layer **433**, a transparent conduction layer **434**, and a common wiring **460**. The common wiring **460** is electrically connected with the transparent conduction layer **434** of the PIN photodiode **423** through a contact hole **451**. The conventional PIN photodiode **423** of the TFT-PIN array substrate **420** has a metal layer **431** spread on the whole surface. Thus, the long-wavelength ultraviolet ray having a wavelength of 365 nm (UVA) cannot penetrate metal layer **431**. Consequently, UV curable LOCA is hard to cure in the conventional PIN photodiode **423** of the TFT-PIN array substrate **420**. Therefore, UV curable LOCA cannot apply to the fabrication of the conventional assembly structure of flat-panel X-ray detectors.

SUMMARY OF THE INVENTION

[0007] The primary objective of the present invention is to provide a TFT-PIN array substrate and an assembly structure for a flat-panel X-ray detector, wherein the metal layer of the PIN photodiode of the TFT-PIN array substrate is perforated to have a hole allowing UV-light to pass through the TFT-PIN array substrate, whereby UV curable LOCA can be cured by UV-light, and whereby UV curable LOCA can be applied to assemble the scintillator substrate and the TFT-PIN array substrate, and whereby is increased the detective quantum efficiency and promoted the quality of medical X-ray images.

[0008] To achieve the abovementioned objective, the present invention proposes a TFT-PIN array substrate for a flat-panel X-ray detector, which comprises a first substrate; a TFT and a PIN photodiode formed on the first substrate. The PIN photodiode includes a metal layer, a photoelectric conduction layer, and a first transparent conduction layer. The photoelectric conduction layer is formed on the metal layer and excited by external light to generate electrons and holes. The first transparent conduction layer is formed on the photoelectric conduction layer. The metal layer is perforated to have at least one hole, which allows external light to pass through the metal layer.

[0009] The present invention also proposes an assembly structure for a flat-panel X-ray detector, which comprises a scintillator substrate; an adhesive layer made of UV curable LOCA and formed on the scintillator; and a TFT-PIN array substrate stuck to the scintillator substrate by the adhesive layer. The TFT-PIN array substrate includes a first substrate; a TFT and a PIN photodiode formed on the first substrate. The PIN photodiode includes a metal layer, a photoelectric conduction layer, and a first transparent conduction layer. The photoelectric conduction layer is formed on the metal layer and excited by external light to generate electrons and holes. The first transparent conduction layer is formed on the photoelectric conduction layer. The metal layer is perforated to have at least one hole, which allows external light (UV-light) to pass through and cure UV curable LOCA, whereby the scintillator substrate and the TFT-PIN array substrate are assembled together. The UV curable LOCA has a viscosity of about 2000-3000 CPS.

[0010] The photoelectric conduction layer of the PIN photodiode includes an n-type doped amorphous silicon layer; an undoped intrinsic amorphous silicon layer; and a p-type doped amorphous silicon layer. The first transparent conduc-

tion layer is made of a transparent electric conduction material, such as ITO (Indium Tin Oxide) or IZO (Indium Zinc Oxide). In one embodiment, the PIN photodiode further includes a second transparent conduction layer, which is arranged between the metal layer and the photoelectric conduction layer to increase the capacitance of the PIN photodiode.

[0011] In the assembly structure for a flat-panel X-ray detector, TFT includes a gate wiring, a gate insulation layer, a semiconductor island, a data transmission wiring, a dielectric layer and a common wiring. The gate wiring is formed on the first substrate and includes a gate line and a gate electrically connected with the gate line. The gate insulation layer covers the gate wiring and the first substrate. The semiconductor island is formed on the gate insulation layer and exactly above the gate. The data transmission wiring is formed on the gate insulation layer and includes a data line, a source and a drain. The data line intersects the gate line. The source and the drain are extended to the semiconductor island and separated in said semiconductor island. The drain electrically connects with the data line. The source electrically connects with the metal layer of the PIN photodiode. The dielectric layer covers the data transmission wiring and the PIN photodiode and includes one or more contact holes. The common wiring is formed on the dielectric layer and electrically connected with the first transparent conduction layer of the PIN photodiode through the contact hole.

[0012] Below, embodiments are described in detail in cooperation with drawings to make easily understood the objectives, characteristics and accomplishments of the present invention.

BRIEF DESCRIPTION OF THE DRAWINGS

[0013] FIGS. 1-3 are diagrams schematically conventional assembly structures for a flat-panel X-ray detector;

[0014] FIG. 4 is a diagram schematically showing an assembly structure for a flat-panel X-ray detector according to one embodiment of the present invention;

[0015] FIG. 5A is a diagram showing a conventional TFT-PIN array substrate with Section Line A-A thereon;

[0016] FIG. 5B is a diagram schematically showing a TFT-PIN array substrate with Section Line B-B thereon according to one embodiment of the present invention;

[0017] FIG. 6 is a sectional view taken along Section Line A-A in FIG. 5A;

[0018] FIG. 7 is a sectional view taken along Section Line B-B in FIG. 5B; and

[0019] FIG. 8 is a sectional view schematically showing a TFT-PIN array substrate for a flat-panel X-ray detector according to another embodiment of the present invention.

DETAILED DESCRIPTION OF THE INVENTION

[0020] The present invention proposes a TFT-PIN array substrate and an assembly structure for a flat-panel X-ray detector, which are suitable to a UV curable LOCA-based process. Refer to FIG. 4 a diagram schematically showing an assembly structure for a flat-panel X-ray detector according to one embodiment of the present invention. The assembly structure of the present invention comprises a TFT-PIN array substrate **100**, an adhesive layer **200**, and a scintillator substrate **300**. The TFT-PIN array substrate **100** includes a first substrate; a TFT and a PIN photodiode formed on the first substrate, which will be described in detail hereinafter. The

scintillator substrate **300** includes a second substrate **310** and a scintillator **320** formed on the second substrate **310**. The TFT-PIN array substrate **100** is faced to the scintillator **320** of the scintillator substrate **300** and stuck to the scintillator substrate **300** by the adhesive layer **200**, which is made of UV curable LOCA and formed between the TFT-PIN array substrate **100** and the scintillator substrate **300**. The UV curable LOCA has a viscosity of about 2000-3000 CPS.

[0021] In the conventional technology, UV-light is unlikely to pass through the scintillator substrate and the TFT-PIN array substrate to cure UV curable LOCA. Therefore, the conventional technology cannot assemble the scintillator substrate and the TFT-PIN array substrate with a UV curable LOCA-based method. In the present invention, the metal layer of the PIN photodiode of the TFT-PIN array substrate **100** is perforated to allow UV-light to pass through the TFT-PIN array substrate **100**. Therefore, UV curable LOCA can be cured by UV-light to assemble the scintillator substrate and the TFT-PIN array substrate in the present invention. Below, embodiments are used to demonstrate the structure and principle of the TFT-PIN array substrate **100**.

[0022] Refer to FIG. 5B a diagram schematically showing a TFT-PIN array substrate **100** with Section Line B-B thereon according to one embodiment of the present invention. Also refer to FIG. 7 a sectional view taken along Section Line B-B in FIG. 5B.

[0023] A gate wiring is made of a metallic material and formed on TFT **120** disposed on a first substrate **110**. The gate wiring includes a gate line **122** extending transversely and a gate **123** electrically connecting with the gate line **122**. A gate insulation layer **124** covers the gate wiring and the first substrate **110**. A semiconductor island **125** is formed on the gate insulation layer and exactly above the gate **123**. A data transmission wiring is made of a metallic material and formed on the gate insulation layer **124**. The data transmission wiring includes a data line **127** extending longitudinally and intersecting the gate line **122**, a drain **128** extending to the semiconductor island **125**, and a source **129** also extending to the semiconductor island **125**. The drain **128** and the source **129** are separated in the semiconductor island **125**. The drain **128** electrically connects with the data line **127**. The source **129** electrically connects with a metal layer **131**, which is within the coverage of a PIN photodiode **130**. The metal layer **131** is perforated to have a single hole **132**, which penetrates the metal layer **131** and reveals the gate insulation layer **124** below the metal layer **131**. However, the present invention does not limit the number of the holes **132**.

[0024] A photoelectric conduction layer **133** is formed on the metal layer **131** and excited by external light to generate electrons and holes. The photoelectric conduction layer **133** includes an n-type doped amorphous silicon layer; an undoped intrinsic amorphous silicon layer; and a p-type doped amorphous silicon layer. A first transparent conduction layer **134** is formed on the photoelectric conduction layer **133** and made of a transparent electric conduction material, such as ITO (Indium Tin Oxide) or IZO (Indium Zinc Oxide). The metal layer **131**, photoelectric conduction layer **133** and first transparent conduction layer **134** jointly form the PIN photodiode **130**.

[0025] A passivation layer **140** covers the data transmission wiring and the metal layer **131**. A dielectric layer **150** covers the PIN photodiode **130**, the passivation layer **140**, and the data transmission wiring and that is below the passivation layer **140**. A plurality of contact holes **151** penetrates the

passivation layer **140** and the dielectric layer **150** to reveal the source **129** and the surface of the first transparent conduction layer **133**. A common wiring **160** is made of a metallic material, formed on the dielectric layer **150**, and extended longitudinally. The common wiring **160** is electrically connected with the first transparent conduction layer **140** of the PIN photodiode **130** through the contact hole **151**, as shown in FIG. SB. A nitride barrier layer **170** is formed over the TFT **120** and the PIN photodiode **130**.

[0026] Refer to FIG. 7 again for an assembly structure for a flat-panel X-ray detector according to the abovementioned embodiment. Via the design of perforating a hole **132** in the PIN photodiode **130** of the TFT-PIN array substrate **100**, external light (especially UVA having a wavelength of 365 nm) is allowed to pass through the TFT-PIN array substrate **100** to cure the adhesive layer **200** made of UV curable LOCA. Therefore, the present invention can assemble the TFT-PIN array substrate **100** and the scintillator substrate **300** in a UV curable LOCA-based method.

[0027] Refer to FIG. 8 a sectional view schematically showing a TFT-PIN array substrate **100** for a flat-panel X-ray detector according to another embodiment of the present invention. In this embodiment, the PIN photodiode **130** further comprises a second transparent conduction layer **135** in addition to the metal layer **131**, photoelectric conduction layer **133** and first transparent conduction layer **134**. The second transparent conduction layer **135** is formed between the metal layer **131** and the photoelectric conduction layer **133**. The second transparent conduction layer **135** is made of a transparent electric conduction material, such as ITO (Indium Tin Oxide) or IZO (Indium Zinc Oxide). The second transparent conduction layer **135** can increase the capacitance of the PIN photodiode **130**, maintaining the quantity of the stored charges. The hole **132** perforated in the metal layer **131** can increase the transmittance of UV-light.

[0028] In conclusion, the present invention discloses a TFT-PIN array substrate and an assembly structure for a flat-panel X-ray detector, wherein holes are perforated in the metal layers of the PIN photodiode of the TFT-PIN array substrate to exempt UV-light from being blocked by the metal layer and allow UV-light to pass through the TFT-PIN array substrate to cure UV curable LOCA. Thereby, the adhesive layer made of UV curable LOCA can be used to assemble the TFT-PIN array substrate and the scintillator substrate. Further, the present invention can also increase the detective quantum efficiency and promote the quality of medical X-ray images.

[0029] The embodiments described above are only to exemplify the present invention but not to limit the scope of the present invention. Any equivalent modification or variation according to the spirit of the present invention is to be also included within the scope of the present invention, which is based on the claims stated below.

What is claimed is:

1. A TFT-PIN array substrate for a flat-panel X-Ray detector, comprising
 a first substrate; and
 a thin film transistor (TFT) and a positive-intrinsic-negative (PIN) photodiode formed on said first substrate, wherein said PIN photodiode includes a metal layer, a photoelectric conduction layer and a first transparent conduction layer, and wherein said photoelectric conduction layer is formed on said metal layer and excited by external light to generate electrons and holes, and

wherein said first transparent conduction layer is formed on said photoelectric conduction layer, and wherein said metal layer is perforated to have at least one hole allowing external light to pass through.

2. The TFT-PIN array substrate according to claim 1, wherein said photoelectric conduction layer includes an n-type doped amorphous silicon layer, an undoped intrinsic amorphous silicon layer, and a p-type doped amorphous silicon layer.

3. The TFT-PIN array substrate according to claim 1, wherein said first transparent conduction layer is made of a transparent electric conduction material selected from a group consisting of ITO (Indium Tin Oxide) and IZO (Indium Zinc Oxide).

4. The TFT-PIN array substrate according to claim 1, wherein said PIN photodiode further includes a second transparent conduction layer formed between said metal layer and said photoelectric conduction layer to increase capacitance of said PIN photodiode.

5. The TFT-PIN array substrate according to claim 4, wherein said second transparent conduction layer is made of a transparent electric conduction material selected from a group consisting of ITO (Indium Tin Oxide) and IZO (Indium Zinc Oxide).

6. The TFT-PIN array substrate according to claim 1, wherein said TFT includes

a gate wiring formed on said first substrate and having a gate line and a gate electrically connected with said gate line;

a gate insulation layer covering said gate wiring and said first substrate;

a semiconductor island formed on said gate insulation layer and exactly above said gate;

a data transmission wiring formed on said gate insulation layer and including a data line, a source and a drain, wherein said data line intersects said gate line, and wherein said source and said drain are extended to said semiconductor island and separated in said semiconductor island, and wherein said drain electrically connects with said data line, and wherein said source electrically connects with said metal layer of said PIN photodiode; and

a dielectric layer covering said data transmission wiring and said PIN photodiode and including at least one contact hole; and

a common wiring formed on said dielectric layer and electrically connected with said first transparent conduction layer of said PIN photodiode through said contact hole.

7. The TFT-PIN array substrate according to claim 6, wherein said dielectric layer includes a plurality of contact holes penetrating said dielectric layer and respectively revealing surface of said gate and surface of said first transparent conduction layer.

8. The TFT-PIN array substrate according to claim 6, wherein said TFT further includes a passivation layer covering said data transmission wiring and said metal layer, and wherein said dielectric layer covers said passivation layer, and wherein said contact holes penetrate said passivation layer and said dielectric layer.

9. The TFT-PIN array substrate according to claim 6 further comprising a nitride barrier layer formed over said TFT and said PIN photodiode.

10. The TFT-PIN array substrate according to claim 6, wherein said hole penetrates said metal layer and reveals said gate insulation layer below said metal layer.

11. An assembly structure for a flat-panel X-Ray detector, comprising

- a scintillator substrate;
- an adhesive layer made of a UV (ultraviolet) curable LOCA (Liquid Optically Clear Adhesive) and formed on said scintillator substrate; and
- a TFT-PIN array substrate stuck to said scintillator substrate by said adhesive layer and further comprising a first substrate, and a thin film transistor (TFT) and a positive-intrinsic-negative (PIN) photodiode formed on said first substrate, wherein said PIN photodiode includes a metal layer, a photoelectric conduction layer and a first transparent conduction layer, and wherein said photoelectric conduction layer is formed on said metal layer and excited by external light to generate electrons and holes, and wherein said first transparent conduction layer is formed on said photoelectric conduction layer, and wherein said metal layer is perforated to have at least one hole allowing external light to pass through to cure said UV curable LOCA and assemble said scintillator substrate and said TFT-PIN array substrate together.

12. The assembly structure for a flat-panel X-Ray detector according to claim 11, wherein said scintillator substrate includes a second substrate and a scintillator, and wherein said scintillator is arranged on said second substrate and faced to said TFT-PIN array substrate.

13. The assembly structure for a flat-panel X-Ray detector according to claim 11, wherein said photoelectric conduction layer includes an n-type doped amorphous silicon layer, an undoped intrinsic amorphous silicon layer, and a p-type doped amorphous silicon layer.

14. The assembly structure for a flat-panel X-Ray detector according to claim 11, wherein said first transparent conduction layer is made of a transparent electric conduction material selected from a group consisting of ITO (Indium Tin Oxide) and IZO (Indium Zinc Oxide).

15. The assembly structure for a flat-panel X-Ray detector according to claim 11, wherein said PIN photodiode further includes a second transparent conduction layer formed between said metal layer and said photoelectric conduction layer to increase capacitance of said PIN photodiode.

16. The assembly structure for a flat-panel X-Ray detector according to claim 15, wherein said second transparent conduction layer is made of a transparent electric conduction

material selected from a group consisting of ITO (Indium Tin Oxide) and IZO (Indium Zinc Oxide).

17. The assembly structure for a flat-panel X-Ray detector according to claim 11, wherein said TFT includes

- a gate wiring formed on said first substrate and having a gate line and a gate electrically connected with said gate line;
- a gate insulation layer covering said gate wiring and said first substrate;
- a semiconductor island formed on said gate insulation layer and exactly above said gate;
- a data transmission wiring formed on said gate insulation layer and including a data line, a source and a drain, wherein said data line intersects said gate line, and wherein said source and said drain are extended to said semiconductor island and separated in said semiconductor island, and wherein said drain electrically connects with said data line, and wherein said source electrically connects with said metal layer of said PIN photodiode; and
- a dielectric layer covering said data transmission wiring and said PIN photodiode and including at least one contact hole; and
- a common wiring formed on said dielectric layer and electrically connected with said first transparent conduction layer of said PIN photodiode through said contact hole.

18. The assembly structure for a flat-panel X-Ray detector according to claim 17, wherein said dielectric layer includes a plurality of contact holes penetrating said dielectric layer and respectively revealing surface of said gate and surface of said first transparent conduction layer.

19. The assembly structure for a flat-panel X-Ray detector according to claim 17, wherein said TFT further includes a passivation layer covering said data transmission wiring and said metal layer, and wherein said dielectric layer covers said passivation layer, and wherein said contact holes penetrate said passivation layer and said dielectric layer.

20. The assembly structure for a flat-panel X-Ray detector according to claim 17, further comprising a nitride barrier layer formed over said TFT and said PIN photodiode.

21. The assembly structure for a flat-panel X-Ray detector according to claim 17, wherein said hole penetrates said metal layer and reveals said gate insulation layer below said metal layer.

22. The assembly structure for a flat-panel X-Ray detector according to claim 11, wherein said UV curable LOCA has a viscosity of 2000-3000 CPS.

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